# 2112-1024 Bit Static MOS RAM (256 x 4)

GENERAL DESCRIPTION

The 2112 series is high performance, low power static read/write RAMs.

The 2112 series is fabricated with n-channel silicon gate technology which allows the design of high performance easy to use MOS circuits and provides a high functional density on a given monolithic chip.

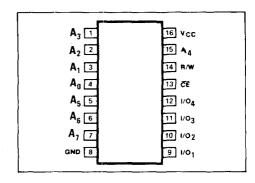
#### **FEATURES**

- Fully static
- No refresh operations, sense amps or clocks required
- Directly TTL compatible
- One 5V power supply

### MAXIMUM RATINGS

PARAMETER		RATING	UNIT
	Temperature range		°c
$T_A$	Operating under bias	0 to 70	
TSTG	Storage	-65 to 150	
	Voltage on any pin with respect to ground	-0.5 to 7	V
$P_{D}$	Power dissipation	1	W

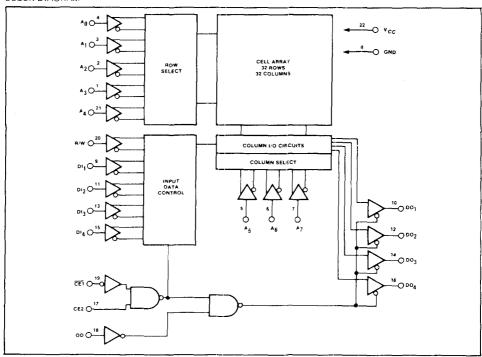
#### CONNECTION DIAGRAM

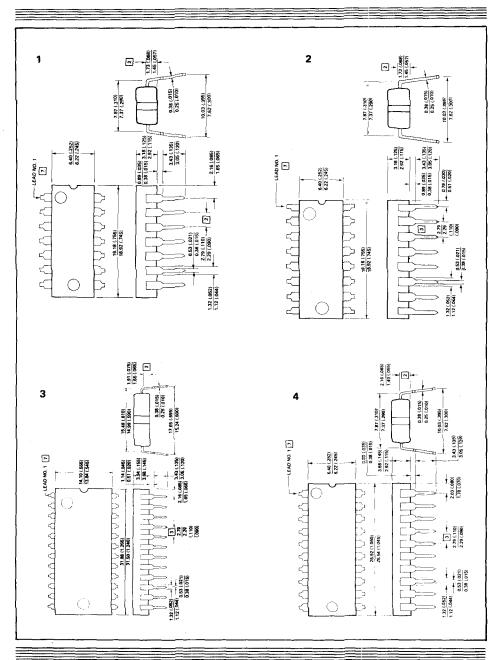


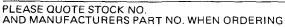
REFERENCE TABLE

TYPE NO.	STOCK NO.	OUTLINE DRWG. NO.	
2112N	56365E	2	

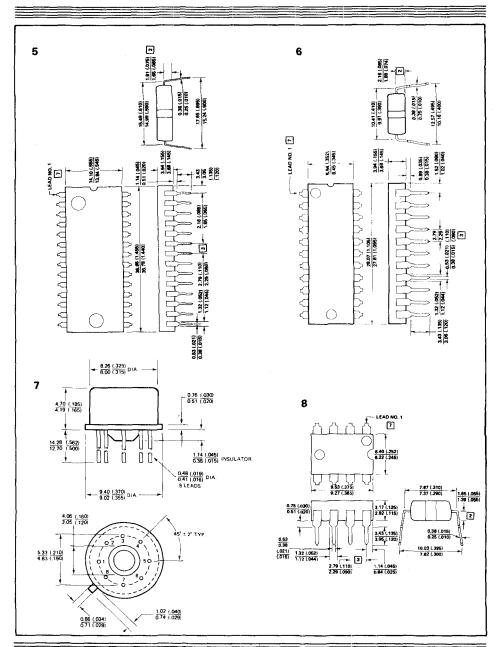
#### BLOCK DIAGRAM





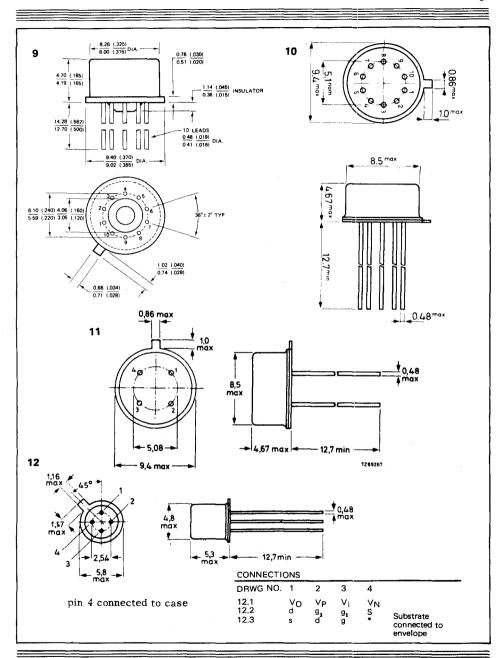








### **Outline Drawings**



PLEASE QUOTE STOCK NO.
AND MANUFACTURERS PART NO. WHEN ORDERING



